

## **isc Silicon NPN Power Transistor**

# **BU2507DF**

#### **DESCRIPTION**

- · High Switching Speed
- High Voltage
- · Built-in Ddamper Ddiode
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

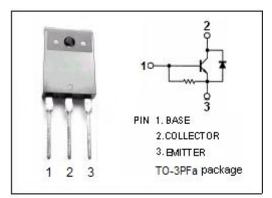
· Designed for use in horizontal deflection circuits of coluor TV receivers and computer monitors.

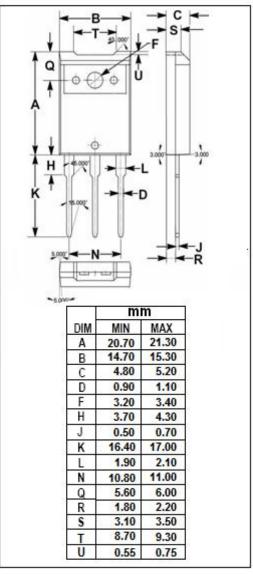
## ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	1500	V	
VCEO	Collector-Emitter Voltage	700	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7.5	V	
Ic	Collector Current-Continuous 8		А	
I <sub>CM</sub>	Collector Current-peak	15	Α	
I <sub>B</sub>	Base Current-Continuous	4	Α	
I <sub>BM</sub>	Base Current-peak	6	А	
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	45	W	
T <sub>j</sub>	Junction Temperature 150		$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-65~150	${\mathbb C}$	

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	2.8	K/W







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#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ;I <sub>B</sub> = 0,L= 25mH	700			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 600mA ;I <sub>C</sub> = 0	7.5	13.5		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A ;I <sub>B</sub> = 0.8A			5.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A ;I <sub>B</sub> = 0.8A			1.1	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = BV <sub>CES</sub> ; V <sub>BE</sub> = 0 V <sub>CE</sub> = BV <sub>CES</sub> ; V <sub>BE</sub> = 0;T <sub>C</sub> =125°C			1.0 2.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7.5V; I <sub>C</sub> = 0		160		mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		14		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 5V	5	7	9	
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 4A			2.0	٧
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V;f <sub>test</sub> = 1MHz		68		pF

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